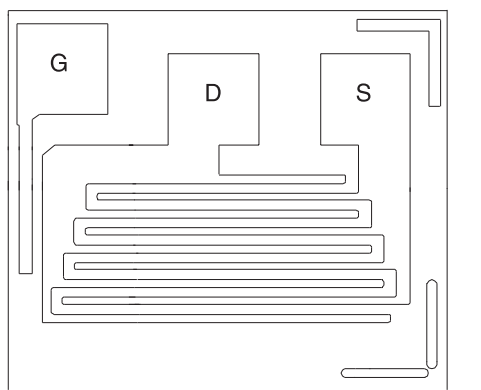


PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	21 x 18 MILS
Die Thickness	8.0 MILS
Drain Bonding Pad Area	3.8 X 3.8 MILS
Source Bonding Pad Area	3.8 X 3.8 MILS
Gate Bonding Pad Area	3.8 X 3.8 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 6,000Å

GEOMETRY



BACKSIDE GATE

GROSS DIE PER 4 INCH WAFER

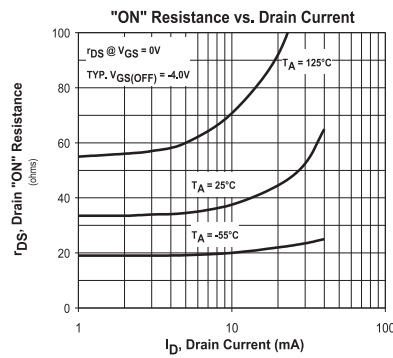
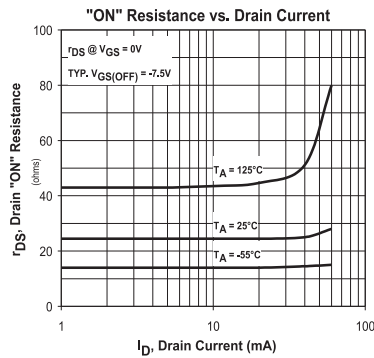
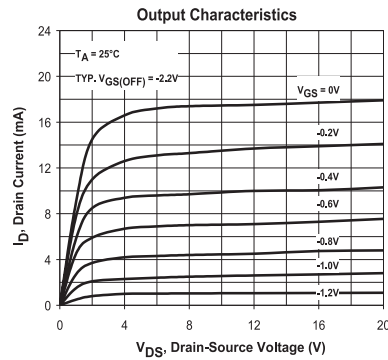
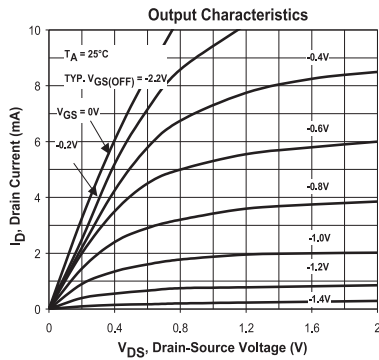
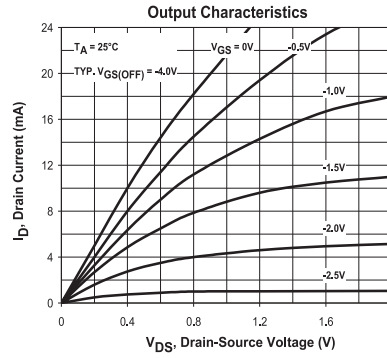
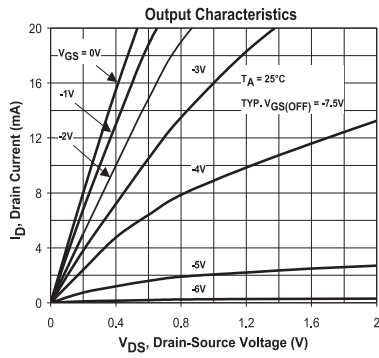
30,950

PRINCIPAL DEVICE TYPES

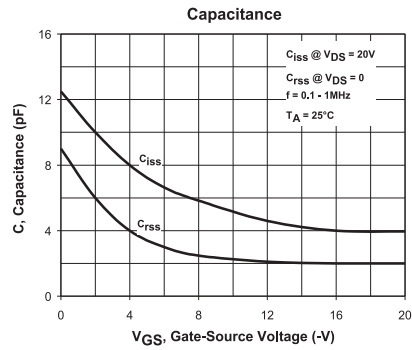
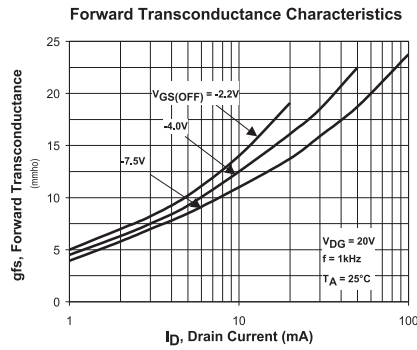
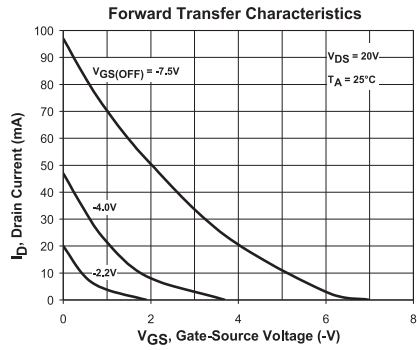
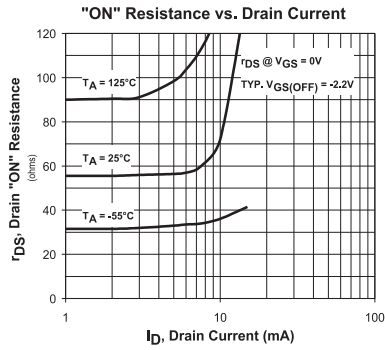
2N4391
2N4392
2N4393
CMPF4391
CMPF4392
CMPF4393

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centalsemi.com

R3 (9 -September 2003)



145 Adams Avenue
 Hauppauge, NY 11788 USA
 Tel: (631) 435-1110
 Fax: (631) 435-1824
 www.centalsemi.com



145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centrasemi.com